

PCN# 20230206000.1 Qualification of additional Fab site (RFAB) and Assembly site (CDAT) options for select LBC7 devices Change Notification / Sample Request

Date: February 06, 2023 To: PREMIER FARNELL PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

Texas Instruments requires acknowledgement of receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If samples or additional data are required, requests must be received within **30 days** of this notification.

The changes discussed within this PCN will not take effect any earlier than the proposed first ship date on Page 3 of this notification, unless customer agreement has been reached on an earlier implementation of the change.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the PCN Team (<u>PCN ww admin team@list.ti.com</u>). For sample requests or sample related questions, contact your local Field Sales Representative.

PCN Team SC Business Services

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE

CUSTOMER PART NUMBER

TLC 59116IPWR TPS 563200DDCT TPS 564201DDCT null null null

Technical details of this Product Change follow on the next page(s).

	February 06,								
				206000.1			PCN Date:		2023
Titl	e:	Qualification select LBC7		ional Fab sit	e (RFAB)	and Asse	mbly si	ite (CDA	T) options for
Cus	stomer (Contact:	PCN	<u> Manager</u>			Dept:		Quality Services
Proposed 1 st Ship Date: May 6, 2023						Sample accept			Mar 6, 2023*
*Sample requests received after March 6, 2023 will not be supported.									
	nge Ty								
	Assemt	oly Site		-	ly Process				nbly Materials
	Design			_	al Specifica				anical Specification
	Test Si			5	Shipping/				Process
		Bump Site Fab Site			ump Mate ab Materia				Bump Process
	wateri	ab Sile			nber chan			water	Tab Flocess
					N Detai	-			
Des	crintio	of Change	•	FC	Detai	3			
	-			announce th	ne qualific.	ation of a	n addit	ional fal	b (RFAB) and
		DAT) site for							
		Current F	ab Site	1		Α	dditioı	nal Fab	Site
С	urrent F Site	ab Proc	ess	Wafer Diameter		itional o Site	Pro	ocess	Wafer Diameter
	MIHO	LBO	27	200 mm		FAB	LBC7		300 mm
For	the devi	ces in the gr	oup 2, c	onstruction	difference			CDAT	
		Mold Cor	npound		SID#C	70141	47	222198	
		Mount Co	mpound	b	SID#P			207123	
		Bond wir diameter	•	osition,	Au, 1.	3 mil	Cu, 0.8 mil		
Qua	I details	are provided	in the (Qual Data Se	ection.				
Rea	ison for	Change:							
	tinuity o								
Ant	icipated	l impact on	Form, I	Fit, Functio	n, Qua lit	y or Reli	ability	(positi	ve / negative):
None									
Im	pact on	Environmer	ital Rat	ings:					
cha	nge. If b ngs.	elow boxes a		ked, there a					ntation of this nvironmental
RoHS REACH						Green Sta	tatus		IEC 62474
	No Char		No C			lo Change			lo Change

ab Site Informatio	identification resulting f		
Chip Site	Chip Site Origin Code (20L)	Chip Site Country C (21L)	ode Chip Site City
MIHO8	MH8	JPN	Ibaraki
RFAB	RFB	USA	Richardson
sembly Site Infor	mation:		
Assembly Site	Assembly Site Origin (22L)	Assembly Country ((23L)	Code Assembly City
UTL1	NSE	THA	Bangkok
UTL3	UT3	THA	Bangpakong
CDAT	CDA	CHN	Chengdu
2DC: 20[: MSL`2 /260C/1 YEAR MSL 1 /235C/UNLIM DPT:	G4 SEAL DT 03/29/04	(1P) SN74LS07 (Q) 2000 (31T) LOT: 399 (4W) TKY (1T) (P)	(D) 0336 59047MLA 7523483812
INSTRUMENTS MADE IN: Malaysia 20C: 20; MSL '2 /260C/1 YEAR MSL 1 /235C/UNLIM PPT: TEM.	03/29/04 06 39	(a) 2000	(D) 0336 59047MLA 7523483512 21L) CC0:USA
INSTRUMENTS MADE IN: Malaysia DC: 29: ISL '2 /260C/1 YEAR ISL 1 /235C/UNLIM OPT: TEM: BL: 5A (L)TO oduct Affected:	03/29/04 06 39	(Q) 2000 (31T)LOT: 39! (4W)TKY(1T) (P) (2P) REV: (20L) CSO: SHE (22L) ASO: MLA	(D) 0336 59047MLA 7523483512 21L) CC0:USA
INSTRUMENTS TADE IN: Malaysia 20: 20: 1SL'2 /260C/1 YEAR 1SL 1 /235C/UNLIM PT: TEM: .BL: 5A (L)TO oduct Affected: oup 1 Devices Add	³⁹ 1750 ling RFAB as an addition	(Q) 2000 (31T)LOT: 39! (4W)TKY(1T) (P) (2P) REV: (20L) CSO: SHE (22L) ASO: MLA	(D) 0336 59047MLA 7523483512 21L) CC0:USA
INSTRUMENTS MADE IN: Malaysia DC: 29: ISL 2 /260C/1 YEAR ISL 1 /235C/UNLIM PT: TEM: BL: 5A (L)TO oduct Affected: oup 1 Devices Add N1102023DBZR	03/29/04 39 1750 100 RFAB as an addition SN2101029RVER	(Q) 2000 (31T)LOT: 399 (4W) TKY(1T) (P) (2D) REV: (20L) CSO: SHE (22L) ASO: MLA (22L) ASO: MLA	(D) 0336 59047MLA 7523483512 21L) CCO:USA 23L) ACO: MYS
INSTRUMENTS TADE IN: Malaysia DC: 29: TSL 2 /260C/1 YEAR ISL 1 /235C/UNLIM PT: TEM: BL: 5A (L)TO oduct Affected: oup 1 Devices Add N1102023DBZR N1102023LP	39 39 1750 Ing RF AB as an addition SN2101029RVER TLC59116IPWR	(Q) 2000 (31T)LOT: 399 (4W) TKY(1T) (P) (2P) REV: (20L) CSO: SHE (22L) ASO: MLA (22L) ASO: MLA (22L) ASO: MLA (22L) ASO: MLA	(D) 0336 59047MLA 7523483S12 21L) CC0:USA 23L) AC0: MYS TPS563200DDCR
INSTRUMENTS TADE IN: Malaysia DC: 20: ISL 2 /260C/1 YEAR ISL 1 /235C/UNLIM PT: TEM: BL: 5A (L)TO oduct Affected: oup 1 Devices Add N1102023DBZR N1102023LP N1102023LPB	39 39 1750 Ing RFAB as an addition SN2101029RVER TLC59116IPWR TLC59116IRHBR	(Q) 2000 (31T)LOT: 399 (4W) TKY (1T) (P) (2D) REV: (20L) CSO: SHE (22L) ASO: MLA (22L) ASO: MLA	(D) 0336 59047MLA 7523483512 21L) CCO:USA 23L) ACO: MYS TPS563200DDCR TPS563200DDCT
INSTRUMENTS TABLE IN: Malaysia DC: 20: ISL 2 /260C/1 YEAR ISL 1 /235C/UNLIM PT: TEM: BL: 5A (L)TO oduct Affected: oup 1 Devices Add N1102023DBZR N1102023LP N1102023LPB N1401038RTER	39 39 1750 Ing RFAB as an addition SN2101029RVER TLC59116IPWR TLC59116IRHBR TPS53318DQPR	(Q) 2000 (31T)LOT: 399 (4W) TKY (1T) (P) (2P) REV: (20L) CSO: SHE (22L) ASO: MLA (22L) ASO: MLA	(D) 0336 59047MLA 7523483S12 21L) CC0:USA 23L) ACO: MYS TPS563200DDCR TPS563200DDCR TPS563209DDCR
INSTRUMENTS MADE IN: Malaysia DC: 20: ISL 2 /260C/1 YEAR ISL 1 /235C/UNLIM OPT: TEM: BL: 5A (L)TO Oduct Affected: OUP 1 Devices Add N1102023DBZR N1102023LPB N1102023LPB N1401038RTER N1401043RVER	39 39 1750 Ing RFAB as an addition SN2101029RVER TLC59116IPWR TLC59116IRHBR TPS53318DQPR TPS53318DQPT	(Q) 2000 (31T)LOT: 399 (4W) TKY (1T) (P) (2D) REV: (20L) CSO: SHE (22L) ASO: MLA (20L) CSO: SHE (20L) CSO: SHE ((D) 0336 59047MLA 7523483S12 21L) CCO:USA 23L) ACO: MYS TPS563200DDCR TPS563200DDCR TPS563209DDCR TPS563209DDCR
INSTRUMENTS MADE IN: Malaysia 20: 29: MSL 2 /260C/1 YEAR MSL 1 /235C/UNLIM OTT: TEM: BL: 5A (L)TO Oduct Affected: Oup 1 Devices Add N1102023DBZR N1102023LP N1102023LP N1102023LP N1102023LP N1401038RTER N1401043RVER N1402065RVER	39 39 1750 Ing RFAB as an addition SN2101029RVER TLC59116IPWR TLC59116IRHBR TPS53318DQPR TPS53319DQPR	(Q) 2000 (31T)LOT: 399 (4W) TKY (1T) (P) (2D) REV: (20L) CSO: SHE (22L) ASO: MLA (22L) ASO: MLA	(D) 0336 59047MLA 7523483S12 21L) CCO:USA 23L) ACO: MYS TPS563200DDCR TPS563200DDCR TPS563209DDCR TPS563209DDCR TPS563209DDCT TPS563210ADDFR
INSTRUMENTS MADE IN: Malaysia 2DC: 29: MSL 2 /260C/1 YEAR MSL 1 /235C/UNLIM OPT: ITEM: LBL: 5A (L)TO roduct Affected:	39 39 1750 Ing RFAB as an addition SN2101029RVER TLC59116IPWR TLC59116IRHBR TPS53318DQPR TPS53319DQPR TPS53319DQPT	(Q) 2000 (31T) LOT: 399 (4W) TKY (1T) (P) (2D) REV: (20L) CSO: SHE (22L) ASO: MLA (22L) ASO: MLA	(D) 0336 59047MLA 7523483S12 21L) CCO:USA 23L) ACO: MYS TPS563200DDCR TPS563200DDCR TPS563209DDCR TPS563209DDCT TPS563210ADDFR TPS563210ADDFT
INSTRUMENTS MADE IN: Malaysia 20: MSL 2 /260C/1 YEAR MSL 1 /235C/UNLIM OPT: ITEM: LBL: 5A (L)TO roduct Affected: roup 1 Devices Add SN1102023DBZR SN1102023LPB SN1102023LPB SN1401038RTER SN1401043RVER SN1402065RVER SN1402065RVET	39 39 1750 Ing RFAB as an addition SN2101029RVER TLC59116IPWR TLC59116IRHBR TPS53318DQPR TPS53319DQPR TPS53319DQPT TPS53513RVER	(Q) 2000 (31T)LOT: 399 (4W) TKY (1T) (P) (2D) REV: (20L) CSO: SHE (22L) ASO: MLA (20L) CSO: SHE (22L) CSO: SHE	(D) 0336 59047MLA 7523483S12 21L) CCO:USA 23L) ACO: MYS TPS563200DDCR TPS563200DDCR TPS563209DDCR TPS563209DDCR TPS563210ADDFR TPS563210ADDFT TPS563210DDFR
INSTRUMENTS MADE IN: Malaysia 20C: 20: MSL 2 /260C/1 YEAR MSL 1 /235C/UNLIM OPT: ITEM: LBL: 5A (L)TO TODUCT Affected: TOUD 1 Devices Add SN1102023LP SN1102023LP SN1102023LP SN1102023LP SN1401038RTER SN1401043RVER SN1401043RVER SN1402065RVER SN1402065RVET SN1501019ADDCR	39 39 1750 Ing RFAB as an addition SN2101029RVER TLC59116IPWR TLC59116IRHBR TPS53318DQPR TPS53319DQPR TPS53319DQPT TPS53319DQPT TPS53513RVER TPS53513RVER-P	(Q) 2000 (31T) LOT: 399 (4W) TKY (1T) (P) (2D) REV: (20L) CSO: SHE (22L) ASO: MLA (22L) ASO: MLA	(D) 0336 59047MLA 7523483S12 21L) CCO:USA 23L) ACO: MYS TPS563200DDCR TPS563200DDCR TPS563209DDCR TPS563209DDCT TPS563210ADDFR TPS563210DDFR TPS563210DDFR TPS563210DDFT

SN1501020DDCT	TPS53515RVET	TPS548A20RVET	TPS563219DDFT
SN1504025DDCR	TPS53913RVER	TPS548B22RVFR	TPS564201DDCR
SN1504025DDCT	TPS53913RVET	TPS548B22RVFT	TPS564201DDCT
SN1504026DDCR	TPS53915RVER	TPS549A20RVER	TPS564208DDCR
SN1504026DDCT	TPS53915RVET	TPS549A20RVET	TPS564208DDCT
SN1602018RVFR	TPS543B20RVFR	TPS549B22RVFR	TPS82084SILR
SN1602018RVFT	TPS543B20RVFT	TPS549B22RVFT	TPS82084SILT
SN1607018DQPR	TPS543C20ARVFR	TPS55340PWP	TPS82085SILR
SN1607021DQPR	TPS543C20RVFR	TPS55340PWPR	TPS82085SILT
SN1611045DDCR	TPS543C20RVFT	TPS55340RTER	TPSM41615MOVR
SN1804026DDFR	TPS544A20RVFR	TPS55340RTET	TPSM41625MOVR

TPS548A20RVER-P

TPS53515RVER

Texas Instruments Incorporated

SN1501020DDCR

TI Information - Selective Disclosure

PCN# 20230206000.1

TPS563219DDFR

SN1804026DDFT	TPS544A20RVFT	TPS562200DDCR	TPSM846C23MOLR
SN1807012RVFR	TPS544B20RVFR	TPS562200DDCT	TPSM846C24MOLR
SN1807013RVER	TPS544B20RVFT	TPS562209DDCR	
SN1812002RVFR	TPS544C20RVFR	TPS562209DDCT	

Group 2 Devices Adding RFAB Fab site and CDAT as an additional Assembly site:								
TPS62240DRVR	TPS62250DRVT	TPS62262DRVR	TPS62291DRVT					
TPS62240DRVT	TPS62260ADRVR	TPS62262DRVT	TPS62293DRVR					
TPS62242DRVR	TPS62260ADRVT	TPS62263DRVR	TPS62562DRVR					
TPS62242DRVT	TPS62260DRVR	TPS62263DRVT	TPS62562DRVT					
TPS62243DRVR	TPS62260DRVT	TPS62290DRVR	TPS62590DRVR					
TPS62243DRVT	TPS62261DRVR	TPS62290DRVT	TPS62590DRVT					
TPS62250DRVR	TPS62261DRVT	TPS62291DRVR						

Qualification Report

Approve Date 6-October-2010

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: TPS51217DSC
ED	Electrical Characterization	Per Datasheet Parameters	Pass
HAST	Biased HAST, 130C/85%RH	96 Hours	3/231/0
AC	Autoclave, 121C	96 Hours	3/231/0
HBM	ESD - HBM	2000 V	3/9/0
CDM	ESD - CDM	500 V	3/9/0
HTOL	Life Test, 135C	635 Hours	3/231/0
HTSL	High Temp. Storage Bake, 170C	420 Hours	3/231/0
LU	Latch-up	(per JESD78)	3/18/0
TC	Temperature Cycle, -65/150C	500 Cycles	3/18/0

- Qual Device TPS51217DSC is qualified at LEVEL2-260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent TEMP Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines) Approved 15-Feb-2022

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>TP\$62261TDRVRQ1</u>	QBS Package Reference: <u>Q25171QWDRCRQ1</u>
			Test Group A	A – Accele	rated Env	ironment Stress Tests			
	PC	A1	JEDEC J-STD-020 JESD22-A113	3		MSL2/260C	-	3/693/0	3/693/0
	HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 hours	1/77/0 & QBS	3/231/0
\square	AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 hours	3/231/0	3/231/0
	тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 cycles	3/231/0	3/231/0
	TC- WBP	A4	MIL-STD883 Method 2011	1	60	Bond Pull over Ball Post T/C 500 Cycles	Wires	QBS	1/30/0
	PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	1/45/0
	HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 150C	1000 hours	QBS	3/231/0
			Test Group E	3 – Accele	rated Life	time Simulation Tests			
	HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 hours	B1 Data carried over from original TPS62261TDRVRQ1 qualification	
	ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 hours	B2 Data carried over from original TPS62261TDRVRQ1 qualification	
	EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	
			Test Group	o C – Pack	age Asse	mbly Integrity Tests			
	WBS	C1	AEC Q100-001	1	30	Wire Bond Shear (Cpk>1.67)	-	1/30/0	
	WBS	C1	AEC Q100-001	1	30	Wire Bond Shear, Cpk >1.67	Wires	1/30/0	
	SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Free Solder	QBS to package family data	1/15/0
	SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb Solder	QBS to package family data	1/15/0

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>TP 562261TDRVRQ1</u>	QBS Package Reference: <u>Q25171QWDRCRQ1</u>
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	QBS to package family data	3/30/0
		Test Grou	ıp D – Die	Fabricatio	on Reliability Tests			
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	Completed Per Process Technology Requirements	-
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-
		Test Gi	oup E – E	lectrical V	erification Tests			
НВМ	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	E2 Data carried over from original TPS62261TDRVRQ1 qualification	
CDM	E3	AEC Q100-011	1	3	ESD - CDM	500 V	E3 Data carried over from original TPS62261TDRVRQ1 qualification	
LU	E4	AEC Q100-004	1	6	Latch-up	Per AEC Q100-004	E4 Data carried over from original TPS62261TDRVRQ1 qualification	
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67	E5 Data carried over from original TPS62261TDRVRQ1 qualification	

- QBS: Qual By Similarity

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +125°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold : HTOL, ED Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room : AC/uHAST

Green/Pb-free Status: Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the contact below or your local Field Sales Representative.

Location	E-Mail			
WW Change Management Team	PCN ww admin team@list.ti.com			

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